

SPTECH Silicon PNP Power Transistor

BD808

DESCRIPTION

- DC Current Gain -
: $h_{FE} = 30 @ I_C = -2A$
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = -60V(\text{Min})$
- Complement to Type BD807

APPLICATIONS

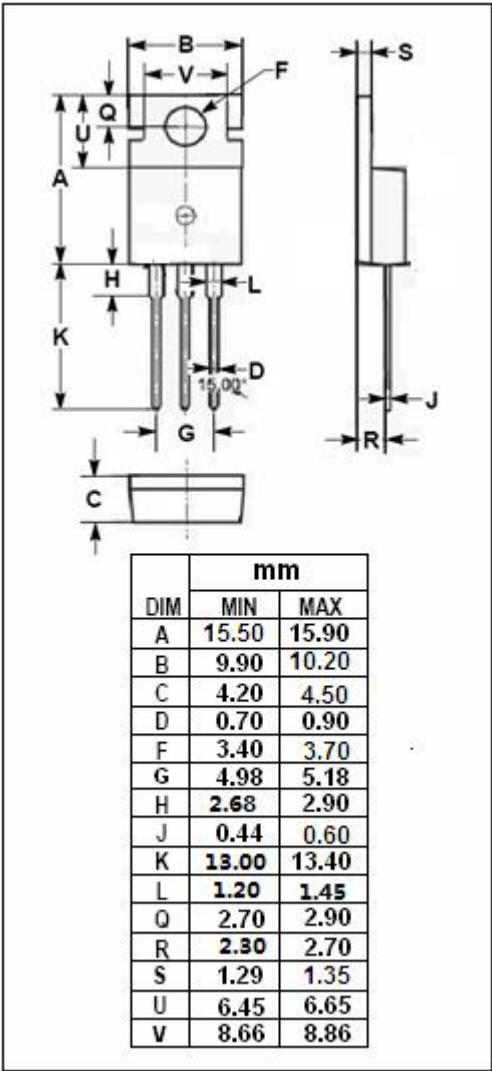
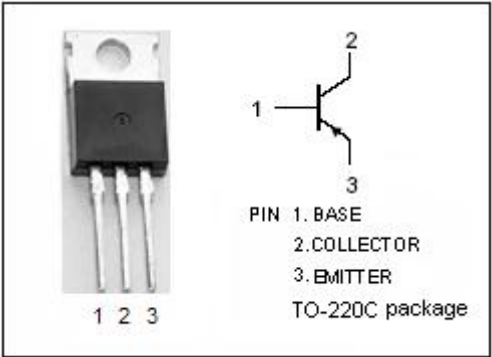
- Designed for use in high power audio amplifiers utilizing complementary or quasi complementary circuits.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-70	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-10	A
I_B	Base Current	-6	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	90	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.39	$^{\circ}C/W$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = -30\text{mA}$; $I_B = 0$	-60		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -4\text{A}$; $I_B = -0.4\text{A}$		-1.1	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -4\text{A}$; $V_{CE} = -2\text{V}$		-1.6	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -70\text{V}$; $I_E = 0$		-1.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}$; $I_C = 0$		-2.0	mA
h_{FE-1}	DC Current Gain	$I_C = -2\text{A}$; $V_{CE} = -2\text{V}$	30		
h_{FE-2}	DC Current Gain	$I_C = -4\text{A}$; $V_{CE} = -2\text{V}$	15		
f_T	Current-Gain—Bandwidth Product	$I_C = -1.0\text{A}$; $V_{CE} = -10\text{V}$; $f_{test} = 1.0\text{MHz}$	1.5		MHz